

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS396

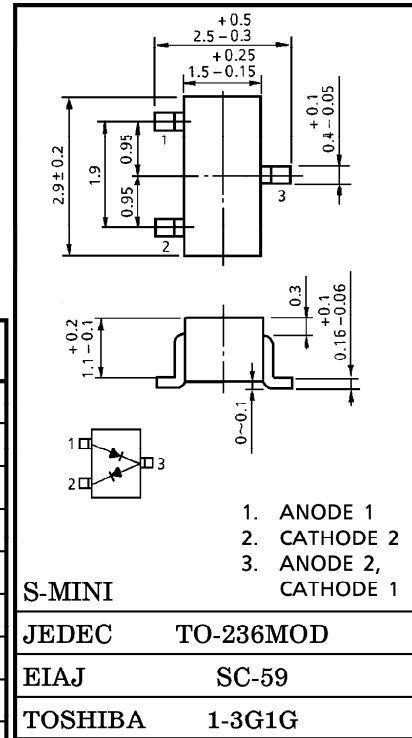
LOW VOLTAGE HIGH SPEED SWITCHING

Unit in mm

- Low Forward Voltage : $V_F(3) = 0.54V$ (Typ.)
- Low Reverse Current : $I_R = 5\mu A$ (Max.)
- Small Package : SC-59

MAXIMUM RATINGS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | RATING | UNIT |
|--------------------------------|-----------|---------|------------|
| Maximum (Peak) Reverse Voltage | V_{RM} | 45 | V |
| Reverse Voltage | V_R | 40 | V |
| Maximum (Peak) Forward Current | I_{FM} | 300 * | mA |
| Average Forward Current | I_O | 100 * | mA |
| Surge Current (10ms) | I_{FSM} | 1 * | A |
| Power Dissipation | P | 150 | mW |
| Junction Temperature | T_j | 125 | $^\circ C$ |
| Storage Temperature Range | T_{stg} | -55~125 | $^\circ C$ |
| Operation Temperature Range | T_{opr} | -40~100 | $^\circ C$ |



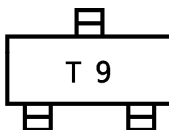
Weight : 0.012g

* : Unit Rating. Total Rating=Unit Rating×0.7

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

| CHARACTERISTIC | SYMBOL | TEST CONDITION | MIN. | TYP. | MAX. | UNIT |
|-------------------|----------|---------------------|------|------|------|---------|
| Forward Voltage | $V_F(1)$ | $I_F = 1mA$ | — | 0.28 | — | V |
| | $V_F(2)$ | $I_F = 10mA$ | — | 0.36 | — | |
| | $V_F(3)$ | $I_F = 100mA$ | — | 0.54 | 0.60 | |
| Reverse Current | I_R | $V_R = 40V$ | — | — | 5 | μA |
| Total Capacitance | C_T | $V_R = 0, f = 1MHz$ | — | 18 | 25 | pF |

MARKING



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